

TCS600

600 Watts, 50 Volts, Pulsed Avionics 1030 MHz

GENERAL DESCRIPTION

The TCS600 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030/1090 MHz, with the pulse width and duty required for TCAS applications. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55ST Style 1

ABSOLUTE MAXIMUM RATINGS

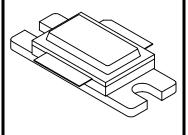
Maximum Power Dissipation

Device Dissipation @25°C 1458 W

Maximum Voltage and Current

Maximum Temperatures

Storage Temperature -65 to +200 °C Operating Junction Temperature +230 °C



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 1030 MHz	600			W
P _{in}	Power Input	$V_{CC} = 50 \text{ Volts}$			80	W
P_g	Power Gain	$PW = 32 \mu sec$	8.7			dB
$\eta_{\rm c}$	Collector Efficiency	DF = 1%		50		
Pd	Pulse Droop			0.5		dB
VSWR	Load Mismatch Tolerance	F = 1030 MHz			4:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

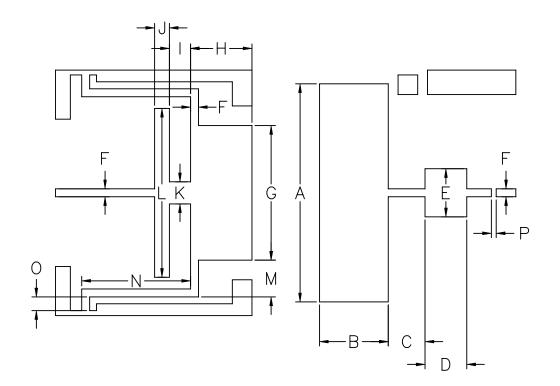
BV _{ebo} *	Emitter to Base Breakdown	Ie = 50 mA	3.5		V
BV_{ces}	Collector to Emitter Breakdown	Ic = 100 mA	65		V
h _{FE} *	DC – Current Gain	Vce = 5V, Ic = 5A	20		
θjc^1	Thermal Resistance			0.12	°C/W

NOTE 1: At rated output power and pulse conditions.

Initial Issue MAY 1999

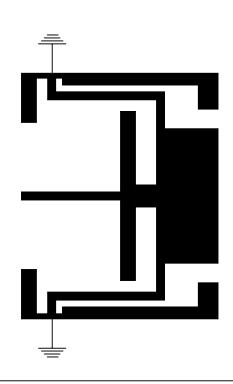
^{*:} Not measureable due to internal EB returns.

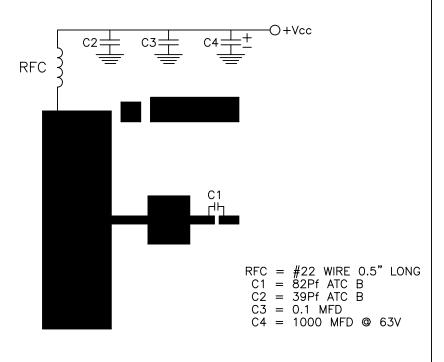




DIM	INCHES		
Α	2.220		
В	.700		
С	.375		
D	.425		
Ε	.490		
F	.081		
G	1.370		
Н	.625		
- 1	.216		
J	.150		
K	.225		
L	1.720		
М	.375		
N	1.108		
0	.140		
Р	.050		

MATERIAL = TEFLON FIBRE GLASS DIELECTRIC THICKNESS = 0.030" Er = 2.55







DWG NO.

TCS600